

# HIGH ISOLATION VOLTAGE HIGH COLLECTOR TO EMITTER VOLTAGE TYPE SOP MULTI PHOTOCOUPLER

-NEPOC Series-

## DESCRIPTION

The PS2703-1 is an optically coupled isolator containing a GaAs light emitting diode and an NPN silicon phototransistor.

This is mounted in a plastic SOP (Small Outline Package) for high density applications.

This package has shield effect to cut off ambient light.

## FEATURES

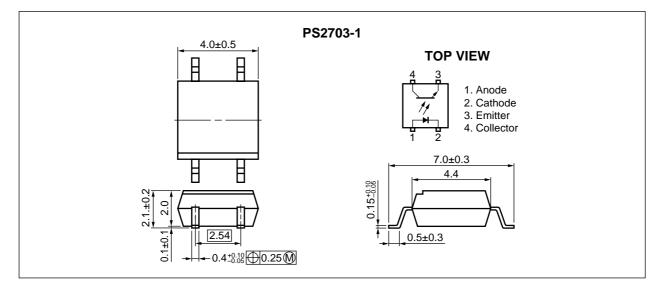
- High isolation voltage (BV = 3 750 Vr.m.s.)
- High collector to emitter voltage (VcEO = 120 V)
- SOP (Small Outline Package) type
- Each isolated channel per package
- High-speed switching (it, tr = 10 µs TYP.)
- Taping product number: PS2703-1-F3, F4
- Safety standards
  - UL approved: File No. E72422
  - BSI approved: File No. 8219/8220
  - CSA approved: File No. CA 101391
  - DIN EN60747-5-2 (VDE0884 Pat2) approved (Option)

## **APPLICATIONS**

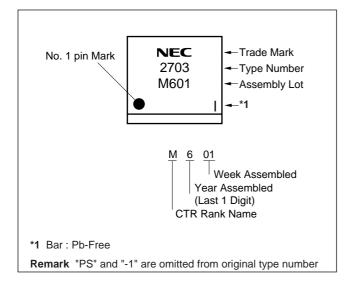
- Hybrid IC
- Telephone/FAX
- FA/OA equipment
- Programmable logic controllers
- Power supply

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## PACKAGE DIMENSIONS (in millimeters)



## ★ MARKING EXAMPLE



## **\*** ORDERING INFORMATION

Part Number	Order Number	Solder Plating Specification	Packing Style	Safety Standard Approval	Application Part Number*1
PS2703-1	PS2703-1-A	Pb-Free	Magazine case 100 pcs	Standard products	PS2703-1
PS2703-1-F3	PS2703-1-F3-A		Embossed Tape 3 500 pcs/reel	(UL, BSI, CSA	
PS2703-1-F4	PS2703-1-F4-A			approved)	
PS2703-1-V	PS2703-1-V-A		Magazine case 100 pcs	DIN EN60747-5-2	
PS2703-1-V-F3	PS2703-1-V-F3-A		Embossed Tape 3 500 pcs/reel	(VDE0884 Part2)	
PS2703-1-V-F4	PS2703-1-V-F4-A			Approved (Option)	

\*1 For the application of the Safety Standard, following part number should be used.

	Parameter	Symbol	Ratings	Unit
Diode	Forward Current (DC)	lF	50	mA
	Reverse Voltage	VR	6	V
	Power Dissipation Derating	⊿P₀/°C	0.8	mW/°C
	Power Dissipation	PD	80	mW
	Peak Forward Current*1	IFP	1	А
Transistor	Collector to Emitter Voltage	Vceo	120	V
	Emitter to Collector Voltage	Veco	6	V
	Collector Current	lc	30	mA
	Power Dissipation Derating	⊿Pc/°C	1.5	mW/°C
	Power Dissipation	Pc	150	mW
Isolation Voltage <sup>*2</sup>		BV	3 750	Vr.m.s.
Operating Ambient Temperature		TA	–55 to +100	°C
Storage Temperature		Tstg	–55 to +150	°C

# ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C, unless otherwise specified)

\*1 PW = 100 *µ*s, Duty Cycle = 1%

\*2 AC voltage for 1 minute at  $T_A = 25$ °C, RH = 60% between input and output Pins 1-2 shorted together, 3-4 shorted together.

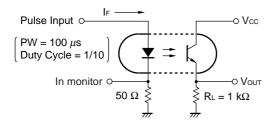
	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	VF	IF = 5 mA		1.1	1.4	V
	Reverse Current	Ir	V <sub>R</sub> = 5 V			5	μA
	Terminal Capacitance	Ct	V = 0 V, f = 1 MHz		30		pF
Transistor	Collector to Emitter Dark Current	ICEO	IF = 0 mA, Vce = 120 V			100	nA
Coupled	Current Transfer Ratio	CTR	IF = 5 mA, Vce = 5 V	50	150	400	%
	(Ic/I <sub>F</sub> ) <sup>*1</sup>		IF = 1 mA, VCE = 5 V	10	80		
	Collector Saturation Voltage	Vce (sat)	I⊧ = 10 mA, lc = 2 mA			0.3	V
	Isolation Resistance	Rı-o	VI-O = 1 kVDC	10 <sup>11</sup>			Ω
	Isolation Capacitance	Сі-о	V = 0 V, f = 1 MHz		0.4		pF
	Rise Time *2	tr	$V_{CC} = 5 \text{ V}, \text{ Ic} = 2 \text{ mA}, \text{ R}_{L} = 1 \text{ k}\Omega$		10		μS
	Fall Time *2	tr			10		

## ELECTRICAL CHARACTERISTICS (TA = 25 °C)

## \*1 CTR rank

CTR rank	CTR (%)	Conditions
к	200 to 400	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$
	80 to	$I_F = 1 \text{ mA}, V_{CE} = 5 \text{ V}$
L	100 to 300	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$
	25 to	$I_F = 1 \text{ mA}, V_{CE} = 5 \text{ V}$
М	50 to 150	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$
	10 to	$I_F = 1 \text{ mA}, V_{CE} = 5 \text{ V}$

\*2 Test circuit for switching time



DIODE POWER DISSIPATION vs.

100

10

1.0

TRANSISTOR POWER DISSIPATION vs.

#### AMBIENT TEMPERATURE AMBIENT TEMPERATURE 100 200 Transistor Power Dissipation Pc (mW) Diode Power Dissipation PD (mW) 75 150 1.5 mW/°C 50 100 25 50 0 25 50 75 100 0 25 50 75 Ambient Temperature TA (°C) Ambient Temperature T<sub>A</sub> (°C) COLLECTOR CURRENT vs. FORWARD CURRENT vs. FORWARD VOLTAGE COLLECTOR TO EMITTER VOLTAGE 100 10 5 mA ጽ 2 4 mA 8 +100 °C Forward Current IF (mA) $T_A =$ Collector Current Ic (mA) 10 +75 °C ₹ +50 °C 6 3 mA 1 +25 °C 0 °C 2 mA 25 °C 0.1 -55 °C 2 1 mA 0.5 mA 0.01 **–** 0.6 0.8 1.0 1.2 1.4 1.6 0 2 4 6 8 Forward Voltage VF (V) Collector to Emitter Voltage VCE (V) COLLECTOR CURRENT vs. COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE COLLECTOR SATURATION VOLTAGE 50 000 Collector to Emitter Dark Current Iceo (nA) 10 $I_F = 25 \text{ mA}$ 10 mA 10 000 5 000 5 mA 5 Collector Current Ic (mA) 2.5 mA 1 000 2 mA40 V 500 1.5 mA 24 V 100 50 10 V 1 mA 0.5 10 5 0.5 mA<sup>-</sup> 0.5 0.1 -60 0.1∟ 0.0 -40 0 20 40 60 80 100 0.2 0.4 0.6 0.8 -20 Ambient Temperature T<sub>A</sub> (°C) Collector Saturation Voltage VCE (sat) (V)

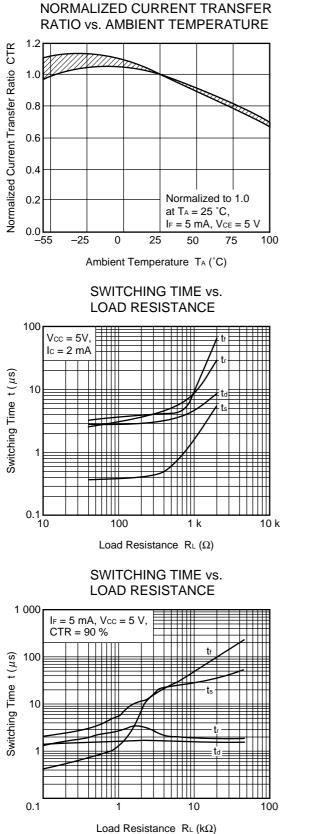
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25℃, unless otherwise specified)

Remark The graphs indicate nominal characteristics.

Data Sheet PN10242EJ02V0DS

50

VCE = 5 V



Forward Current I⊧ (mA) FREQUENCY RESPONSE

0**□** 0.1

0.5 1

300

250

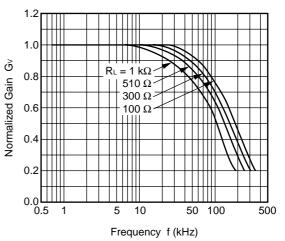
200

150

100

50

Current Transfer Ratio CTR (%)

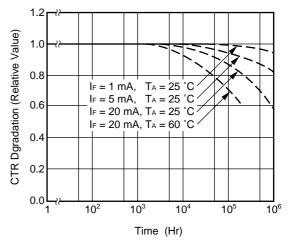


CURRENT TRANSFER RATIO vs.

5 10

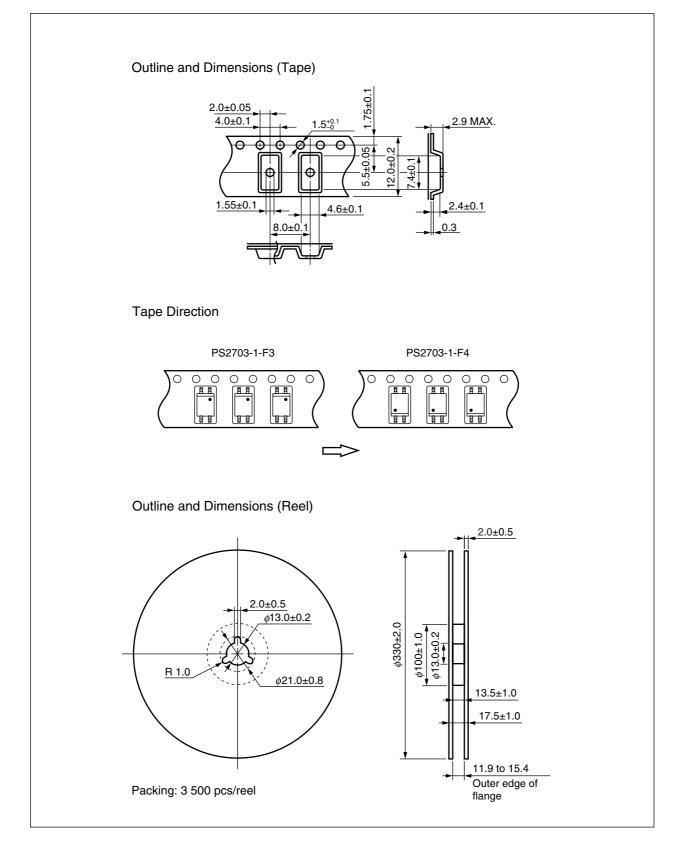
FORWARD CURRENT

LONG TIME CTR DEGRADATION



Remark The graphs indicate nominal characteristics.

## **TAPING SPECIFICATIONS (in millimeters)**



## NOTES ON HANDLING

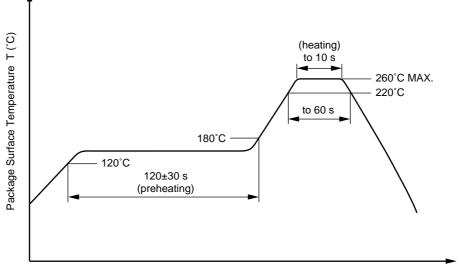
## 1. Recommended soldering conditions

## (1) Infrared reflow soldering

- Peak reflow temperature
- Time of peak reflow temperature
- Time of temperature higher than 220C
- Time to preheat temperature from 120 to 180C
- Number of reflows
- Flux

260C or below (package surface temperature) 10 seconds or less 60 seconds or less 120±30 s Three Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

#### Recommended Temperature Profile of Infrared Reflow



Time (s)

#### (2) Wave soldering

- Temperature 260C or below (molten solder temperature)
- Time 10 seconds or less
- Preheating conditions 120C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
- Flux Rosin flux containing small amount ofchlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

#### ★ (3) Soldering by soldering iron

Peak temperature (ead part temperature)	350°C or below
Time (each pins)	3 seconds or less
• Flux	Rosin flux containing small amount of chlorine (The flux with a
	maximum chlorine content of 0.2 Wt% is recommended.)

- (a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead.
- (b) Please be sure that the temperature of the package would not be heated over 100°C.

## (4) Cautions

## • Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

## 2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output or between collector-emitters at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

#### \* 3. Measurement conditions of current transfer ratios (CTR), which differ according to photocoupler

Check the setting values before use, since the forward current conditions at CTR measurement differ according to product.

When using products other than at the specified forward current, the characteristics curves may differ from the standard curves due to CTR value variations or the like. Therefore, check the characteristics under the actual operating conditions and thoroughly take variations or the like into consideration before use.

## USAGE CAUTIONS

- 1. Protect against static electricity when handling.
- 2. Avoid storage at a high temperature and high humidity.

# SPECIFICATION OF VDE MARKS LICENSE DOCUMENT (VDE0884)

Parameter	Symbol	Speck	Unit
Application classification (DIN VDE 0109)			
for rated line voltages $\leq$ 300 Vr.m.s.		IV	
for rated line voltages $\leq$ 600 Vr.m.s.		Ш	
Climatic test class (DIN IEC 68 Teil 1/09.80)		55/100/21	
Dielectric strength maximum operating isolation voltage.			
Test voltage (partial discharge test procedure a for type test and random test)	UIORM	710	V <sub>peak</sub>
U <sub>pr</sub> = 1.2 × U <sub>IORM</sub> , P <sub>d</sub> < 5 pC	Upr	850	V <sub>peak</sub>
Test voltage (partial discharge test procedure b for all devices test) $U_{pr} = 1.6 \times U_{IORM}, P_d < 5 pC$	Upr	1 140	Vpeak
Highest permissible overvoltage	Utr	6 000	V <sub>peak</sub>
Degree of pollution (DIN VDE 0109)		2	
Clearance distance		> 5	mm
Creepage distance		> 5	mm
Comparative tracking index (DIN IEC 112/VDE 0303 part 1)	СТІ	175	
Material group (DIN VDE 0109)		III a	
Storage temperature range	Tstg	-55 to +150	°C
Operating temperature range	TA	-55 to +100	°C
Isolation resistance, minimum value			
$V_{IO} = 500 \text{ V} \text{ dc} \text{ at } T_A = 25 ^{\circ}\text{C}$	Ris MIN.	10 <sup>12</sup>	Ω
$V_{IO}$ = 500 V dc at T <sub>A</sub> MAX. at least 100 °C	Ris MIN.	10 <sup>11</sup>	Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve)			
Package temperature	Tsi	150	°C
Current (input current IF, Psi = 0)	lsi	200	mA
Power (output or total power dissipation)	Psi	300	mW
Isolation resistance			
$V_{IO} = 500 \text{ V dc at } T_A = 175 ^\circ\text{C} \text{ (Tsi)}$	Ris MIN.	10 <sup>9</sup>	Ω

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M8E 00.4-0110

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	• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
	<ol> <li>Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.</li> </ol>
	2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
	Do not burn, destroy, cut, crush,or chemically dissolve the product.
	Do not lick the product or in any way allow it to enter the mouth.

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